

Smart Power High-Side-Switch One Channel: 20 m Ω

BTS441T

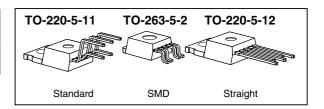




Product Summary

On-state Resistance	RON	$20 m\Omega$
Operating Voltage	Vbb(on)	4.75 41V
Nominal load current	IL(ISO)	21A
Current limitation	IL(lim)	65A

Package



General Description

- N channel vertical power FET with charge pump, ground referenced CMOS compatible input, monolithically integrated in Smart SIPMOS® technology. • Green Product (RoHS compliant)
 - **AEC Qualified**
- Providing embedded protective functions.

Application

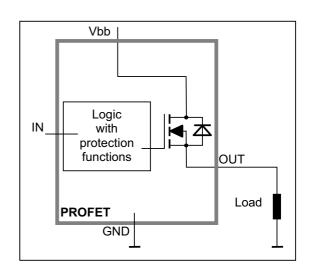
- μC compatible power switch for 5V, 12 V and 24 V DC applications
- All types of resistive, inductive and capacitve loads
- Most suitable for loads with high inrush currents, so as lamps
- Replaces electromechanical relays, fuses and discrete circuits

Basic Funktions

- Very low standby current
- Optimized static electromagnetic compatibility (EMC)
- μC and CMOS compatible
- Fast demagnetization of inductive loads
- Stable behaviour at undervoltage

Protection Functions

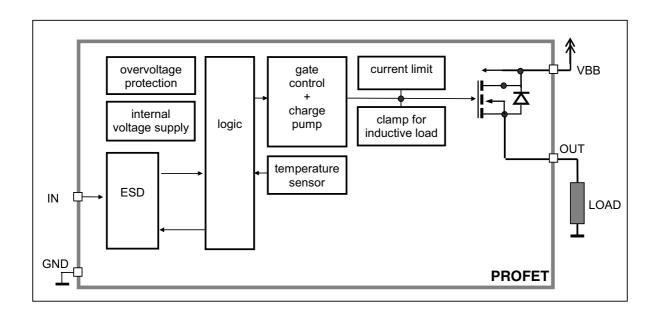
- Short circuit protection
- **Current limitation**
- Overload protection
- Thermal shutdown
- Overvoltage protection (including load dump) with external **GND-resistor**
- Reverse battery protection with external GND-resistor
- Loss of ground and loss of Vbb protection
- Electrostatic discharge (ESD) protection



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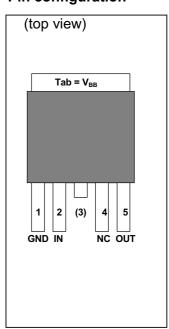
Functional diagram



Pin Definitions and Functions

Pin	Symbol	Function
1	GND	Logic ground
2	IN	Input, activates the power switch in case of logical high signal
3	V _{bb}	Positive power supply voltage The tab is shorted to pin 3
4	N.C.	Not connected
5	OUT	Output to the load
Tab	V _{bb}	Positive power supply voltage The tab is shorted to pin 3

Pin configuration





Maximum Ratings at $T_j = 25$ °C unless otherwise specified

Parameter	Symbol	Values	Unit
Supply voltage (overvoltage protection see page 4)	$V_{ m bb}$	43	V
Supply voltage for full short circuit protection $T_{\rm j \ Start}$ =-40+150°C	V _{bb}	34	V
Load dump protection ¹⁾ $V_{\text{LoadDump}} = V_{\text{A}} + V_{\text{S}}, V_{\text{A}} = 13.5 \text{ V}$ $R_{\text{I}}^{2)} = 2 \Omega$, $R_{\text{L}} = 0.5 \Omega$, $t_{\text{d}} = 200 \text{ ms}$, IN= low or high	V _{Load dump} 3)	60	V
Load current (Short-circuit current, see page 5)	<i>I</i> ∟	self-limited	Α
Operating temperature range Storage temperature range	T _j T _{stg}	-40+150 -55+150	°C
Power dissipation (DC) ; TC≤25°C	P _{tot}	125	W
Maximal switchable inductance, single pulse $V_{bb} = 12V$, $T_{j,start} = 150$ °C, $T_{C} = 150$ °C const. (see diagram, p.8) $I_{L(ISO)} = 21$ A, RL= 0 Ω: $E^{4}_{AS} = 0.7$ J:	Z _L	2.1	mH
Electrostatic discharge capability (ESD) IN: (Human Body Model) Out to all other pins shorted: acc. MIL-STD883D, method 3015.7 and ESD assn. std. S5.1-1993; R=1.5kΩ; C=100pF	V _{ESD}	1.0 8.0	kV
Input voltage (DC)	V _{IN}	-10 +16	V
Current through input pin (DC) see internal circuit diagrams page 7	I _{IN}	±2.0	mA
Thermal resistance chip - case:	R _{thJC}	≤ 1 < 75	K/W
junction - ambient (free air):	R_{thJA}	≤ 75	
SMD version, device on pcb ⁵⁾ :		≤ 33	

Supply voltages higher than $V_{bb(AZ)}$ require an external current limit for the GND pin, e.g. with a 150 Ω resistor in the GND connection. A resistor for the protection of the input is integrated.

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²⁾ $R_{\rm I}$ = internal resistance of the load dump test pulse generator

 $^{^{3)}}$ V_{Load dump} is setup without the DUT connected to the generator per ISO 7637-1 and DIN 40839

⁴⁾ E_{AS} is the maximum inductive switch off energy

Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70μm thick) copper area for V_{bb} connection. PCB is vertical without blown air.



Electrical Characteristics

Parameter and Conditions	Symbol	Values			Unit
at T_j =-40+150°C, V_{bb} = 12 V unless otherwise specified		min	typ	max	
Load Switching Capabilities and Characteristics					
On-state resistance (V _{bb} (pin3) to OUT (pin5)); $I_L = 2 \text{ A V}_{bb} \ge 7\text{V}$: $T_j = 25 \text{ °C}$: $T_j = 150 \text{ °C}$: see diagram page 9	R _{ON}		15 28	20 37	mΩ
Nominal load current (pin 3 to 5) 'ISO 10483-1, 6.7: V _{ON} =0.5V, T _c =85°C	I _{L(ISO)}	17	21		Α
Output current (pin 5) while GND disconnected or GND pulled up ⁶⁾ , V _{bb} =30 V, V _{IN} = 0, see diagram page 7	I _{L(GNDhigh)}			2	mA
Turn-on time IN \perp to 90% V_{OUT} : Turn-off time IN \perp to 10% V_{OUT} : $R_{\text{L}} = 12 \ \Omega,$	$t_{ m on} \ t_{ m off}$	40 40	90 110	200 250	μs
Slew rate on 10 to 30% V_{OUT} , $R_{\text{L}} = 12 \Omega$,	dV/dt _{on}	0.1		1	V/µs
Slew rate off 70 to 40% V_{OUT} , R_{L} = 12 Ω ,	-d V/dt _{off}	0.1		1	V/μs

Operating Parameters

Operating voltage	<i>T</i> _i =-40°C	$V_{ m bb(on)}$	4.75		41	V
	<i>T</i> _j =-40°C <i>T</i> _j =+25°C	22(0)	4.75		43	
	$T_{\rm i} = +105^{\circ}{\rm C}^{(6)}$		4.75		43	
	<i>T</i> _j =+150°C		5.0		43	
Overvoltage protection ⁷⁾	$T_{\rm j}$ =-40°C: $T_{\rm j}$ =+25+150°C:	$V_{\rm bb(AZ)}$	41			V
$I_{bb} = 40 \text{ mA}$	$T_{\rm j}$ =+25+150°C:		43	47	52	
Standby current (pin 3) 8)	T_{j} =-40+25°C: T_{j} =+105°C ⁶): T_{j} =+150°C:	I _{bb(off)}		5	10	μΑ
,	$T_{i}=+105^{\circ}C^{6}$:	` ′			10	•
V _{IN} =0 see diagram page 9	<i>T</i> _j =+150°C:				25	
Off-State output current (include	ded in I _{bb(off)})	I _{L(off)}		1.5	10	μΑ
VIN=0						
Operating current (Pin 1)9), V _{IN} =5 V,		<i>I</i> _{GND}		2	4	mA

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⁶⁾ not subject to production test, specified by design

⁷⁾ see also $V_{
m ON(CL)}$ in table of protection functions and circuit diagram page 7

⁸⁾ Measured with load, typ. 40 μA without load.

⁹⁾ Add I_{IN} , if V_{IN} >5.5 V



Parameter and Conditions	Symbol	Values			Unit	
at $T_j = -40+150$ °C, $V_{bb} = 12$ V unless other		min	typ	max		
Protection Functions ¹⁰⁾						
Current limit (pin 3 to 5)		I _{L(lim)}				
(see timing diagrams, page 9)	T _j =-40°C: T _j =25°C: T _j =+150°C:				85	Α
	$T_j = 25^{\circ}C$:			65		
	<i>T</i> _j =+150°C:		40			
Repetitive short circuit current limit	I _{L(SCr)}		55		Α	
$T_{\rm j} = T_{\rm jt}$ (see timing diagrams, page 10)						
Thermal shutdown time ¹¹⁾¹²⁾ $T_{i,start} = 25^{\circ}C$:		$T_{\rm off(SC)}$		14		ms
(see timing diagram on page 10)						
Output clamp (inductive load switch off)	; <i>T</i> _i =-40°C:		41			V
at VOUT = Vbb - VON(CL), IL= 40 mA	$T_{\rm j}$ =25150°C:	$V_{ON(CL)}$	43	47	52	
Thermal overload trip temperature		T_{jt}	150			°C
Thermal hysteresis	$\Delta T_{\rm jt}$		10		K	
Reverse battery (pin 3 to 1) 13)		- V _{bb}			32	٧
Reverse battery voltage drop $(V_{OUT} > I_L = -2A)$	V _{bb}) Τ _j =+150°C:	-V _{ON(rev)}		540		mV

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¹⁰⁾ Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

¹¹⁾ not subject to production test, specified by design

Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70μm thick) copper area for V_{bb} connection. PCB is vertical without blown air.

Requires 150 Ω resistor in GND connection. The reverse load current through the intrinsic drain-source diode has to be limited by the connected load. Note that the power dissipation is higher compared to normal operating conditions due to the voltage drop across the intrinsic drain-source diode. The temperature protection is not active during reverse current operation! Input and Status currents have to be limited (see max. ratings page 1 and circuit page 7).



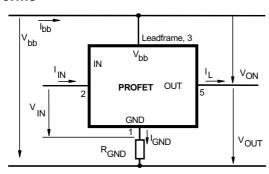
Parameter and Conditions	Symbol	Values			Unit
at T_j =-40+150°C, V_{bb} = 12 V unless otherwise specified		min	typ	max	
Input ¹⁴⁾					
Input resistance see circuit page 7	R_{I}	2.5	3.8	6.5	kΩ
Input turn-on threshold voltage/	$V_{IN(T+)}$	1.2		2.2	V
Input turn-off threshold voltage	V _{IN(T-)}	0.8			V
Input threshold hysteresis	$\Delta V_{IN(T)}$		0.3		V
Off state input current (pin 2) $V_{IN} = 0.4 \text{ V}$:	I _{IN(off)}	1		15	μΑ
On state input current (pin 2) $V_{IN} = 5 \text{ V}$:	I _{IN(on)}	4.5	12	24	μΑ

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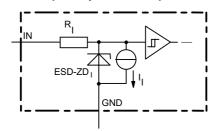
 $^{^{14)}\,\,}$ If a ground resistor R_{GND} is used, add the voltage drop across this resistor.



Terms

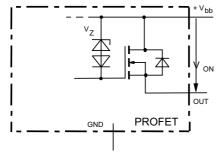


Input circuit (ESD protection)



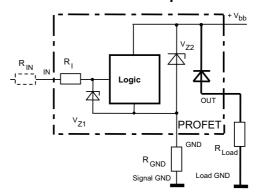
The use of ESD zener diodes as voltage clamp at DC conditions is not recommended.

Inductive and overvoltage output clamp



V_{ON} clamped to 47 V typ.

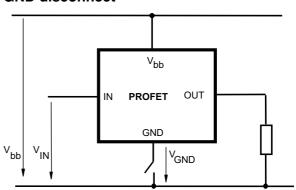
Overvolt. and reverse batt. protection



 V_{Z1} = 6.1 V typ., V_{Z2} = 47 V typ., R_{GND} = 150 Ω, R_{I} = 3.5 kΩ typ.

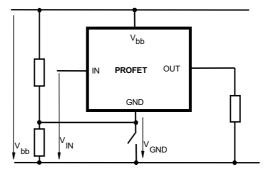
In case of reverse battery the load current has to be limited by the load. Temperature protection is not active

GND disconnect



Any kind of load. In case of Input=high is $V_{OUT} \approx V_{IN}$ - $V_{IN(T+)}$.

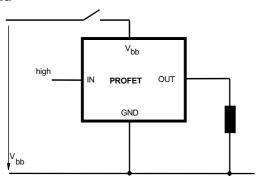
GND disconnect with GND pull up



Any kind of load. If $V_{GND} > V_{IN}$ - $V_{IN(T+)}$ device stays off



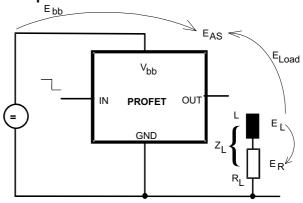
V_{bb} disconnect with charged inductive load



For inductive load currents up to the limits defined by Z_L (max. ratings and diagram on page 8) each switch is protected against loss of V_{bb} .

Consider at your PCB layout that in the case of Vbb disconnection with energized inductive load all the load current flows through the GND connection.

Inductive load switch-off energy dissipation



Energy stored in load inductance:

$$E_{L} = \frac{1}{2} \cdot L \cdot I_{L}^{2}$$

While demagnetizing load inductance, the energy dissipated in PROFET is

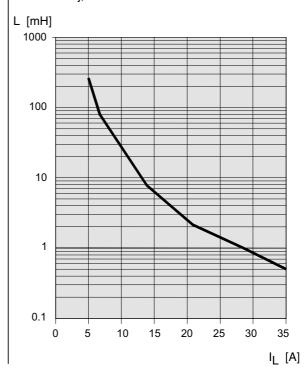
$$E_{AS} = E_{bb} + E_L - E_R = V_{ON(CL)} \cdot i_L(t) dt$$

with an approximate solution for $R_L > 0 \Omega$:

$$E_{\text{AS}} = \frac{I_L \cdot L}{2 \cdot \mathsf{R}_L} \left(\, \mathsf{V}_{\text{bb}} + |\mathsf{V}_{\text{OUT}(\text{CL})}| \right) \; \ln \left(1 + \frac{|L \cdot \mathsf{R}_L}{|\mathsf{V}_{\text{OUT}(\text{CL})}|} \, \right)$$

Maximum allowable load inductance for a single switch off

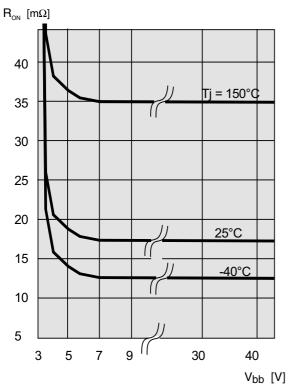
$$L = f(I_L)$$
; T_{j,start} = 150°C, V_{bb} = 12 V, R_L = 0 Ω





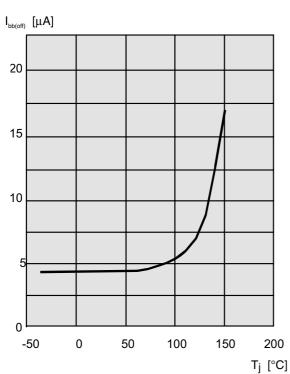
Typ. on-state resistance

 $R_{ON} = f(V_{bb}, T_j); I_L = 2 A, IN = high$



Typ. standby current

 $I_{bb(off)} = f(T_j)$; $V_{bb} = 9...34 \text{ V, IN1,2} = \text{low}$



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Timing diagrams

Figure 1a: V_{bb} turn on:

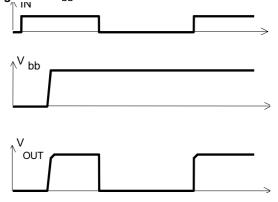


Figure 2a: Switching a resistive load, turn-on/off time and slew rate definition:

proper turn on under all conditions

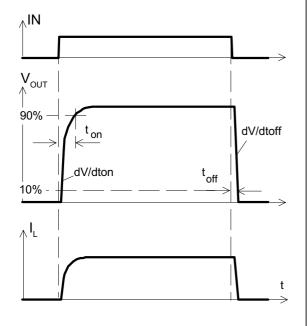


Figure 2b: Switching a lamp,

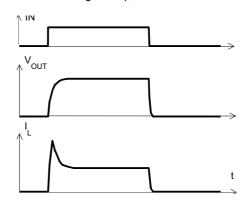


Figure 3a: Short circuit shut down by overtemperature, reset by cooling

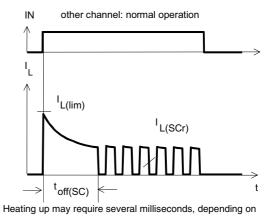
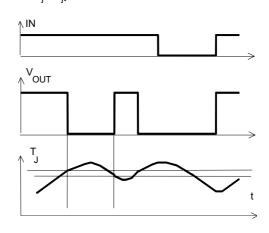


Figure 4a: Overtemperature:

Reset if $T_j < T_{jt}$

external conditions





Package Outlines

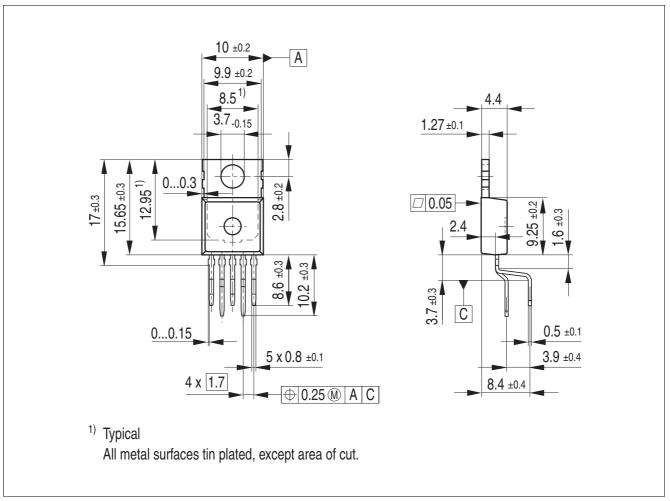


figure 5: PG-TO220-5-11

Green Product (RoHS compliant)

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e Pb-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).



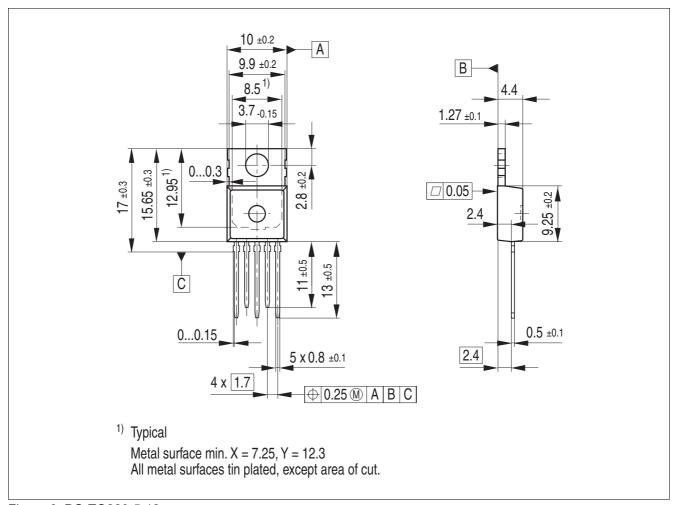


Figure 6: PG-TO220-5-12

Green Product (RoHS compliant)

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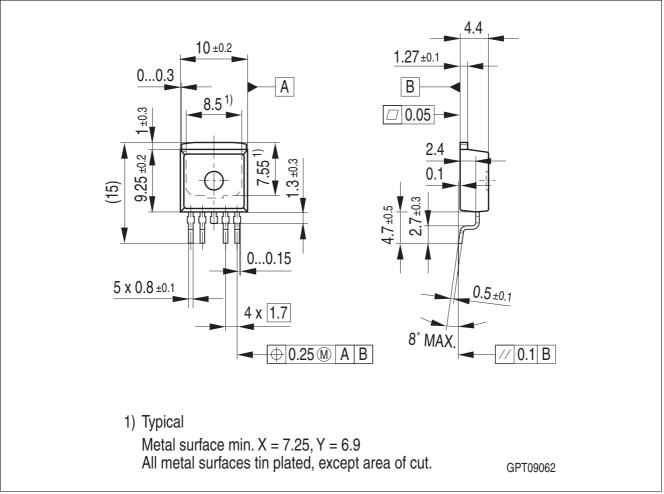


Figure 7: PG-TO263-5-2

Green Product (RoHS compliant)

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Revision History

Revision	Date	Changes
1.11	2008-12-09	RoHS-compliant PG-TO220 and PG-TO263 packages version of the BTS441T All pages: Infineon logo updated
		Page 1:
		Added "AEC qualified" and "RoHS" logo, added "Green Product (RoHS compliant)" and "AEC qualified" statement to feature list, package names changed to RoHS compliant versions, updated package drawing. Page 10-12:
		Package names changed to RoHS compliant versions (PG-TO220-5-11, PG-TO220-12 and PG-TO263-5-2), added "Green Product" description added Revision History added Legal Disclaimer

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